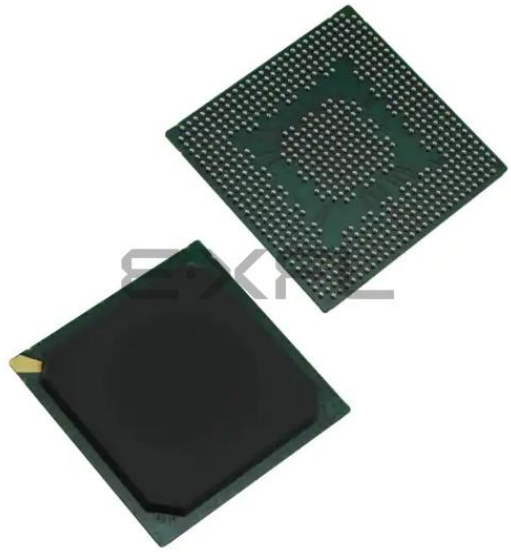


Welcome to E-XFL.COM

Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	266MHz
Co-Processors/DSP	-
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (3)
SATA	-
USB	USB 2.0 + PHY (2)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	-
Package / Case	620-BBGA Exposed Pad
Supplier Device Package	620-HBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8343czqadd

NOTE

The information in this document is accurate for revision 3.x silicon and later (in other words, for orderable part numbers ending in A or B). For information on revision 1.1 silicon and earlier versions, see the *MPC8343E PowerQUICC II Pro Integrated Host Processor Hardware Specifications.*

See Section 22.1, "Part Numbers Fully Addressed by This Document," for silicon revision level determination.

1 Overview

This section provides a high-level overview of the device features. Figure 1 shows the major functional units within the MPC8343EA.

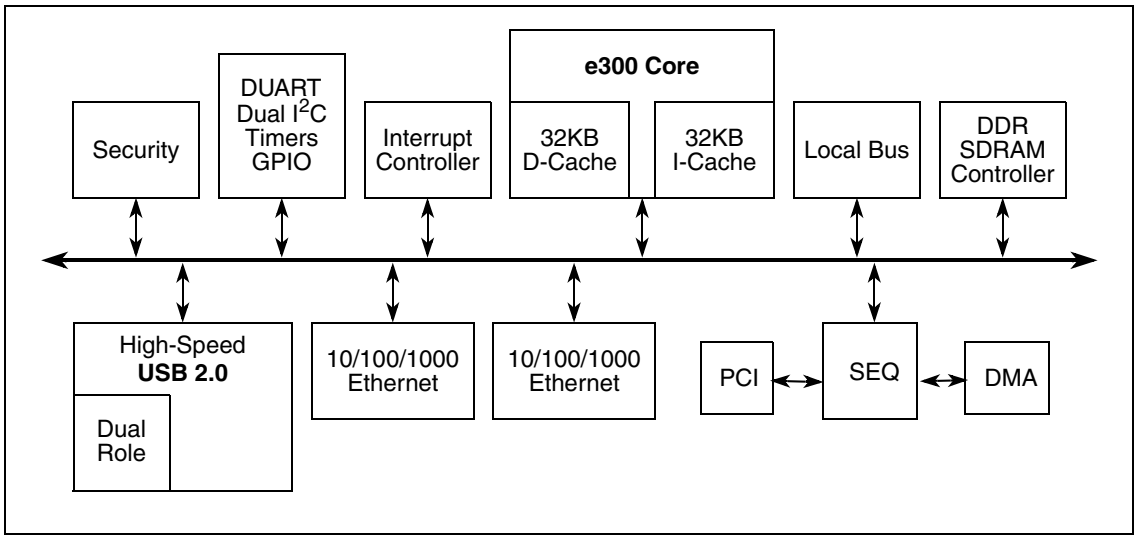


Figure 1. MPC8343EA Block Diagram

Major features of the device are as follows:

- Embedded PowerPC e300 processor core; operates at up to 400 MHz
  - High-performance, superscalar processor core
  - Floating-point, integer, load/store, system register, and branch processing units
  - 32-Kbyte instruction cache, 32-Kbyte data cache
  - Lockable portion of L1 cache
  - Dynamic power management
  - Software-compatible with the other Freescale processor families that implement Power Architecture technology
- Double data rate, DDR1/DDR2 SDRAM memory controller
  - Programmable timing supporting DDR1 and DDR2 SDRAM
  - 32- bit data interface, up to 266 MHz data rate

  - Up to four physical banks (chip selects), each bank up to 1 Gbyte independently addressable
  - DRAM chip configurations from 64 Mbits to 1 Gbit with ×8/×16 data ports
  - Full error checking and correction (ECC) support
  - Support for up to 16 simultaneous open pages (up to 32 pages for DDR2)
  - Contiguous or discontiguous memory mapping
  - Read-modify-write support
  - Sleep-mode support for SDRAM self refresh
  - Auto refresh
  - On-the-fly power management using CKE
  - Registered DIMM support
  - 2.5-V SSTL2 compatible I/O for DDR1, 1.8-V SSTL2 compatible I/O for DDR2
- Dual three-speed (10/100/1000) Ethernet controllers (TSECs)
  - Dual controllers designed to comply with IEEE 802.3™, 802.3u™, 820.3x™, 802.3z™, 802.3ac™ standards
  - Ethernet physical interfaces:
    - 1000 Mbps IEEE Std. 802.3 RGMII, IEEE Std. 802.3z RTBI, full-duplex
    - 10/100 Mbps IEEE Std. 802.3 MII full- and half-duplex
  - Buffer descriptors are backward-compatible with MPC8260 and MPC860T 10/100 programming models
  - 9.6-Kbyte jumbo frame support
  - RMON statistics support
  - Internal 2-Kbyte transmit and 2-Kbyte receive FIFOs per TSEC module
  - MII management interface for control and status
  - Programmable CRC generation and checking
- PCI interface
  - Designed to comply with *PCI Specification Revision 2.3*
  - Data bus width:
    - 32-bit data PCI interface operating at up to 66 MHz
  - PCI 3.3-V compatible
  - PCI host bridge capabilities
  - PCI agent mode on PCI interface
  - PCI-to-memory and memory-to-PCI streaming
  - Memory prefetching of PCI read accesses and support for delayed read transactions
  - Posting of processor-to-PCI and PCI-to-memory writes
  - On-chip arbitration supporting five masters on PCI
  - Accesses to all PCI address spaces
  - Parity supported
  - Selectable hardware-enforced coherency

Table 5 shows the estimated typical I/O power dissipation for MPC8343EA.

Table 5. MPC8343EA Typical I/O Power Dissipation

Interface	Parameter	DDR2 GV_{DD} (1.8 V)	DDR1 GV_{DD} (2.5 V)	OV_{DD} (3.3 V)	LV_{DD} (3.3 V)	LV_{DD} (2.5 V)	Unit	Comments
DDR I/O 65% utilization 2.5 V Rs = 20 Ω Rt = 50 Ω 2 pair of clocks	200 MHz, 32 bits	0.31	0.42	—	—	—	W	—
	266 MHz, 32 bits	0.35	0.5	—	—	—	W	—
PCI I/O load = 30 pF	33 MHz, 32 bits	—	—	0.04	—	—	W	—
	66 MHz, 32 bits	—	—	0.07	—	—	W	—
Local bus I/O load = 25 pF	167 MHz, 32 bits	—	—	0.34	—	—	W	—
	133 MHz, 32 bits	—	—	0.27	—	—	W	—
	83 MHz, 32 bits	—	—	0.17	—	—	W	—
	66 MHz, 32 bits	—	—	0.14	—	—	W	—
	50 MHz, 32 bits	—	—	0.11	—	—	W	—
TSEC I/O load = 25 pF	MII	—	—		0.01	—	W	Multiply by number of interfaces used.
	GMII or TBI	—	—		0.06	—	W	
	RGMII or RTBI	—	—		—	0.04	W	
USB	12 MHz	—	—	0.01	—	—	W	—
	480 MHz	—	—	0.2	—	—	W	—
Other I/O		—	—	0.01	—	—	W	—

4 Clock Input Timing

This section provides the clock input DC and AC electrical characteristics for the device.

4.1 DC Electrical Characteristics

Table 6 provides the clock input (CLKIN/PCI_SYNC_IN) DC timing specifications for the MPC8343EA.

Table 6. CLKIN DC Timing Specifications

Parameter	Condition	Symbol	Min	Max	Unit
Input high voltage	—	V_{IH}	2.7	OV_{DD} + 0.3	V
Input low voltage	—	V_{IL}	–0.3	0.4	V
CLKIN input current	$0 V \le V_{IN} \le OV_{DD}$	I_{IN}	—	±10	μA

Table 16 provides the current draw characteristics for MV_{REF}.

Table 16. Current Draw Characteristics for MV_{REF}

Parameter/Condition	Symbol	Min	Max	Unit	Note
Current draw for MV_{REF}	I_{MVREF}	—	500	μA	1

Note:
1. The voltage regulator for MV_{REF} must supply up to 500 μA current.

6.2 DDR and DDR2 SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR and DDR2 SDRAM interface.

6.2.1 DDR and DDR2 SDRAM Input AC Timing Specifications

Table 17 provides the input AC timing specifications for the DDR2 SDRAM when GV_{DD}(typ) = 1.8 V.

Table 17. DDR2 SDRAM Input AC Timing Specifications for 1.8-V Interface

At recommended operating conditions with GV_{DD} of 1.8 ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	MV_{REF} – 0.25	V	—
AC input high voltage	V_{IH}	MV_{REF} + 0.25	—	V	—

Table 18 provides the input AC timing specifications for the DDR SDRAM when GV_{DD}(typ) = 2.5 V.

Table 18. DDR SDRAM Input AC Timing Specifications for 2.5-V Interface

At recommended operating conditions with GV_{DD} of 2.5 ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	MV_{REF} – 0.31	V	—
AC input high voltage	V_{IH}	MV_{REF} + 0.31	—	V	—

Table 19 provides the input AC timing specifications for the DDR SDRAM interface.

Table 19. DDR and DDR2 SDRAM Input AC Timing Specifications

At recommended operating conditions with GV_{DD} of (1.8 or 2.5 V) ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
Controller Skew for MDQS—MDQ/MECC/MDM	t_{CISKEW}			ps	1, 2
400 MHz		–600	600		3
333 MHz		–750	750		—

Table 19. DDR and DDR2 SDRAM Input AC Timing Specifications (continued)

At recommended operating conditions with GV_{DD} of (1.8 or 2.5 V) ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
266 MHz		–750	750		—
200 MHz		–750	750		—

Notes:

1. t_{CISKEW} represents the total amount of skew consumed by the controller between MDQS[n] and any corresponding bit that will be captured with MDQS[n]. This should be subtracted from the total timing budget.
2. The amount of skew that can be tolerated from MDQS to a corresponding MDQ signal is called t_{DISKEW}. This can be determined by the equation: $t_{DISKEW} = \pm (T/4 - abs(t_{CISKEW}))$; where T is the clock period and abs (t_{CISKEW}) is the absolute value of t_{CISKEW}.
3. This specification applies only to the DDR interface.

Figure 5 illustrates the DDR input timing diagram showing the t_{DISKEW} timing parameter.

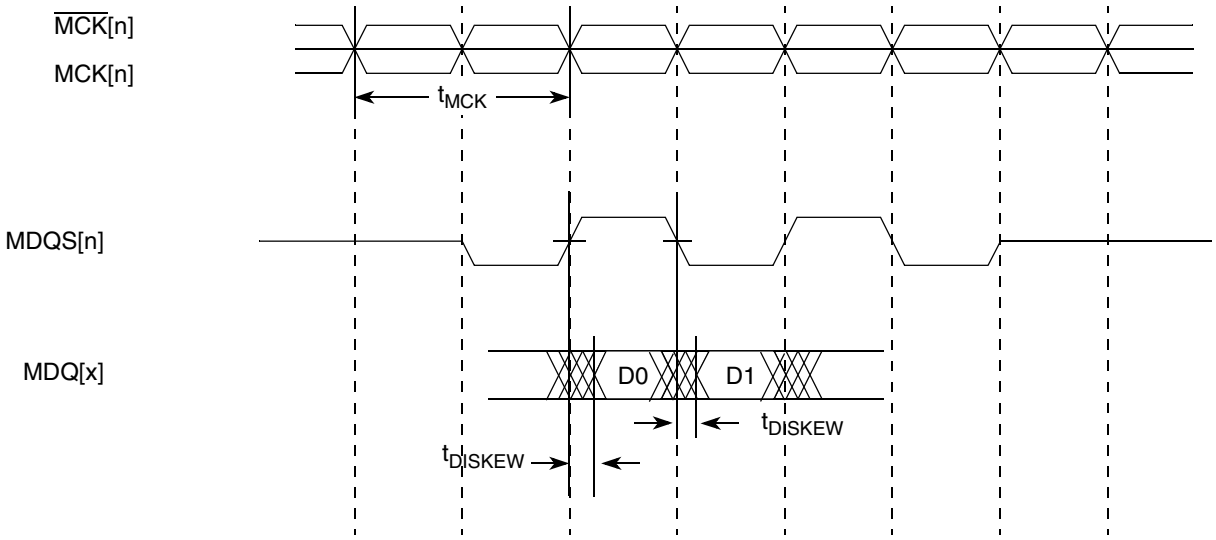


Figure 5. DDR Input Timing Diagram

6.2.2 DDR and DDR2 SDRAM Output AC Timing Specifications

Table 20 shows the DDR and DDR2 output AC timing specifications.

Table 20. DDR and DDR2 SDRAM Output AC Timing Specifications

At recommended operating conditions with GV_{DD} of (1.8 or 2.5 V) ± 5%.

Parameter	Symbol [1]	Min	Max	Unit	Notes
MCK[n] cycle time, (MCK[n]/MCK[n] crossing)	t_{MCK}	7.5	10	ns	2
ADDR/CMD/MODT output setup with respect to MCK	t_{DDKHAS}			ns	3
400 MHz		1.95	—		
333 MHz		2.40	—		
266 MHz		3.15	—		
200 MHz		4.20	—		

Table 20. DDR and DDR2 SDRAM Output AC Timing Specifications (continued)

At recommended operating conditions with GV_{DD} of (1.8 or 2.5 V) ± 5%.

Parameter	Symbol [1]	Min	Max	Unit	Notes
ADDR/CMD/MODT output hold with respect to MCK	t_{DDKHAX}			ns	3
400 MHz		1.95	—		
333 MHz		2.40	—		
266 MHz		3.15	—		
200 MHz		4.20	—		
$\overline{MCS}$(n) output setup with respect to MCK	t_{DDKHCS}			ns	3
400 MHz		1.95	—		
333 MHz		2.40	—		
266 MHz		3.15	—		
200 MHz		4.20	—		
$\overline{MCS}$(n) output hold with respect to MCK	t_{DDKHCX}			ns	3
400 MHz		1.95	—		
333 MHz		2.40	—		
266 MHz		3.15	—		
200 MHz		4.20	—		
MCK to MDQS Skew	t_{DDKHMH}	–0.6	0.6	ns	4
MDQ/MECC/MDM output setup with respect to MDQS	t_{DDKHDS}, t_{DDKLDS}			ps	5
400 MHz		700	—		
333 MHz		775	—		
266 MHz		1100	—		
200 MHz		1200	—		
MDQ/MECC/MDM output hold with respect to MDQS	t_{DDKHDX}, t_{DDKLDX}			ps	5
400 MHz		700	—		
333 MHz		900	—		
266 MHz		1100	—		
200 MHz		1200	—		
MDQS preamble start	t_{DDKHMP}	$-0.5 \times t_{MCK} - 0.6$	$-0.5 \times t_{MCK} + 0.6$	ns	6

Table 21. DUART DC Electrical Characteristics (continued)

Parameter	Symbol	Min	Max	Unit
High-level output voltage, I_{OH} = –100 μA	V_{OH}	OV_{DD} – 0.2	—	V
Low-level output voltage, I_{OL} = 100 μA	V_{OL}	—	0.2	V

7.2 DUART AC Electrical Specifications

Table 22 provides the AC timing parameters for the DUART interface of the MPC8343EA.

Table 22. DUART AC Timing Specifications

Parameter	Value	Unit	Notes
Minimum baud rate	256	baud	—
Maximum baud rate	> 1,000,000	baud	1
Oversample rate	16	—	2

Notes:
1. Actual attainable baud rate will be limited by the latency of interrupt processing.
2. The middle of a start bit is detected as the 8th sampled 0 after the 1-to-0 transition of the start bit. Subsequent bit values are sampled each 16th sample.

8 Ethernet: Three-Speed Ethernet, MII Management

This section provides the AC and DC electrical characteristics for three-speeds (10/100/1000 Mbps) and MII management.

8.1 Three-Speed Ethernet Controller (TSEC)—MII/RGMII/RTBI Electrical Characteristics

The electrical characteristics specified here apply to media independent interface (MII), reduced gigabit media independent interface (RGMII), and reduced ten-bit interface (RTBI) signals except management data input/output (MDIO) and management data clock (MDC). The MII interface is defined for 3.3 V, and the RGMII and RTBI interfaces are defined for 2.5 V. The RGMII and RTBI interfaces follow the Hewlett-Packard *Reduced Pin-Count Interface for Gigabit Ethernet Physical Layer Device Specification*, Version 1.2a (9/22/2000). The electrical characteristics for MDIO and MDC are specified in Section 8.3, "Ethernet Management Interface Electrical Characteristics."

Table 28. MII Management DC Electrical Characteristics Powered at 2.5 V (continued)

Parameter	Symbol	Conditions	Min	Max	Unit
Input high current	I_{IH}	V_{IN}[1] = LV_{DD}	—	10	μA
Input low current	I_{IL}	V_{IN} = LV_{DD}	–15	—	μA

Note:
1. The symbol V_{IN}, in this case, represents the LV_{IN} symbol referenced in Table 1 and Table 2.

Table 29. MII Management DC Electrical Characteristics Powered at 3.3 V

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage (3.3 V)	LV_{DD}	—		2.97	3.63	V
Output high voltage	V_{OH}	I_{OH} = –1.0 mA	LV_{DD} = Min	2.10	LV_{DD} + 0.3	V
Output low voltage	V_{OL}	I_{OL} = 1.0 mA	LV_{DD} = Min	GND	0.50	V
Input high voltage	V_{IH}	—		2.00	—	V
Input low voltage	V_{IL}	—		—	0.80	V
Input high current	I_{IH}	LV_{DD} = Max	V_{IN}[1] = 2.1 V	—	40	μA
Input low current	I_{IL}	LV_{DD} = Max	V_{IN} = 0.5 V	–600	—	μA

Note:
1. The symbol V_{IN}, in this case, represents the LV_{IN} symbol referenced in Table 1 and Table 2.

8.3.2 MII Management AC Electrical Specifications

Table 30 provides the MII management AC timing specifications.

Table 30. MII Management AC Timing Specifications

At recommended operating conditions with LV_{DD} is 3.3 V ± 10% or 2.5 V ± 5%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit	Notes
MDC frequency	f_{MDC}	—	2.5	—	MHz	2
MDC period	t_{MDC}	—	400	—	ns	—
MDC clock pulse width high	t_{MDCH}	32	—	—	ns	—
MDC to MDIO delay	t_{MDKHDX}	10	—	70	ns	3
MDIO to MDC setup time	t_{MDDVKH}	5	—	—	ns	—
MDIO to MDC hold time	t_{MDDXKH}	0	—	—	ns	—
MDC rise time	t_{MDCR}	—	—	10	ns	—

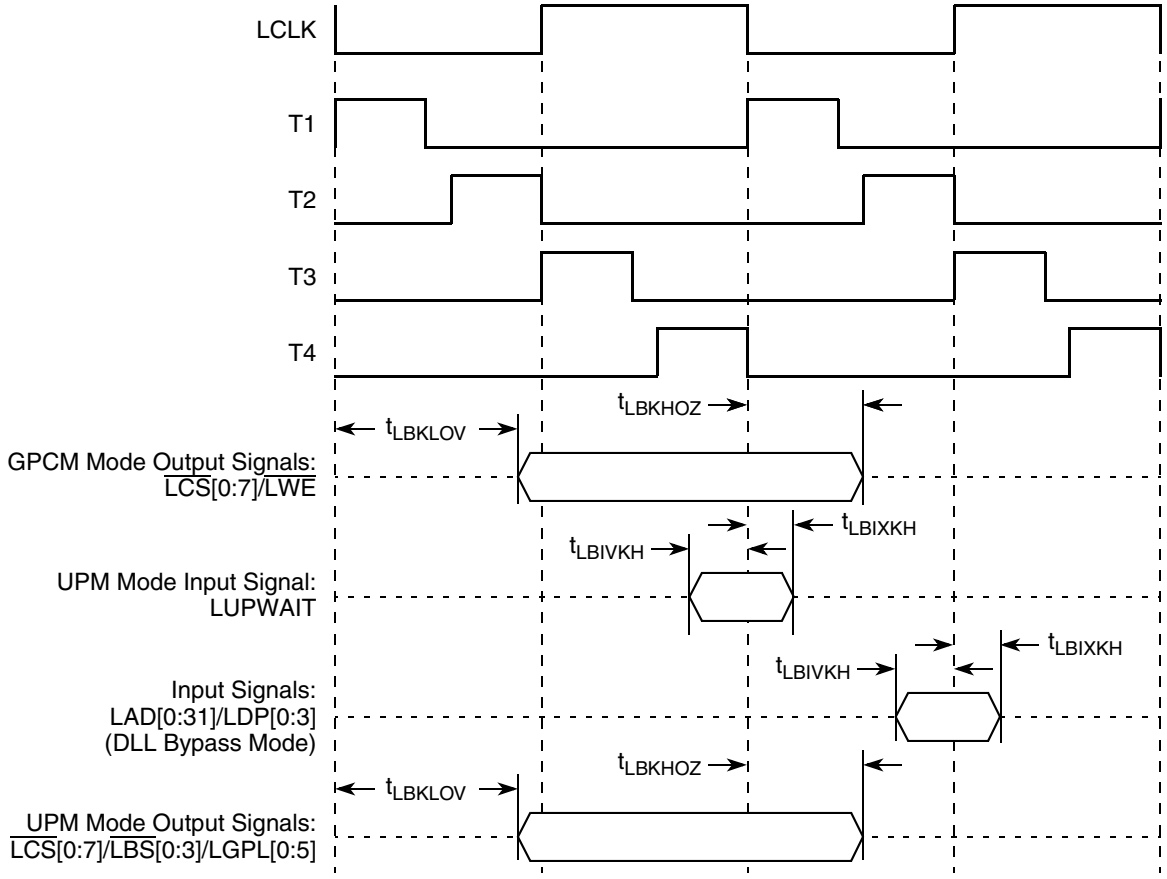


Figure 21. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 4 (DLL Bypass Mode)

Table 37. JTAG AC Timing Specifications (Independent of CLKIN)[1] (continued)

At recommended operating conditions (see Table 2).

Parameter	Symbol[2]	Min	Max	Unit	Notes
JTAG external clock to output high impedance: Boundary-scan data TDO	 t_{JTKLDZ} t_{JTKLOZ}	 2 2	 19 9	ns	5, 6

Notes:

1. All outputs are measured from the midpoint voltage of the falling/rising edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50 Ω load (see Figure 14). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.
2. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{JTDVKH} symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, t_{JTDXKH} symbolizes JTAG timing (JT) with respect to the time data input signals (D) went invalid (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. In general, the clock reference symbol is based on three letters representing the clock of a particular function. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
3. $\overline{\text{TRST}}$ is an asynchronous level sensitive signal. The setup time is for test purposes only.
4. Non-JTAG signal input timing with respect to t_{TCLK}.
5. Non-JTAG signal output timing with respect to t_{TCLK}.
6. Guaranteed by design and characterization.

Figure 23 provides the AC test load for TDO and the boundary-scan outputs of the MPC8343EA.

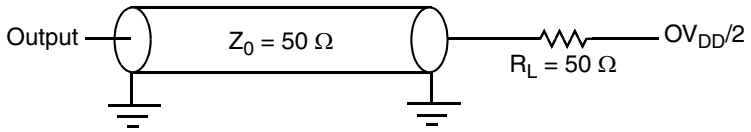


Figure 23. AC Test Load for the JTAG Interface

Figure 24 provides the JTAG clock input timing diagram.

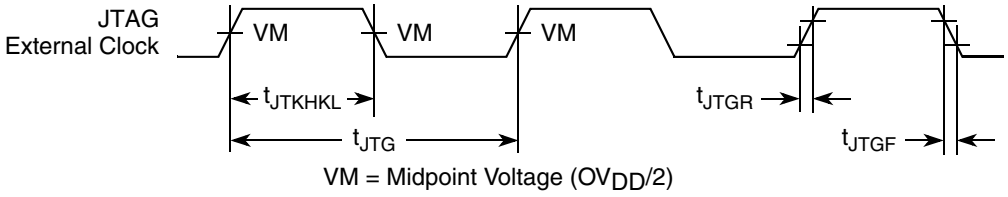


Figure 24. JTAG Clock Input Timing Diagram

Figure 25 provides the $\overline{\text{TRST}}$ timing diagram.

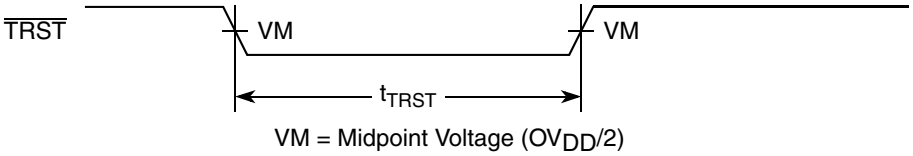


Figure 25. $\overline{\text{TRST}}$ Timing Diagram

12 I²C

This section describes the DC and AC electrical characteristics for the I²C interface of the MPC8343EA.

12.1 I²C DC Electrical Characteristics

Table 38 provides the DC electrical characteristics for the I²C interface of the MPC8343EA.

Table 38. I²C DC Electrical Characteristics

At recommended operating conditions with OV_{DD} of 3.3 V ± 10%.

Parameter	Symbol	Min	Max	Unit	Notes
Input high voltage level	V_{IH}	$0.7 \times OV_{DD}$	$OV_{DD} + 0.3$	V	—
Input low voltage level	V_{IL}	–0.3	$0.3 \times OV_{DD}$	V	—
Low level output voltage	V_{OL}	0	$0.2 \times OV_{DD}$	V	1
Output fall time from V_{IH}(min) to V_{IL}(max) with a bus capacitance from 10 to 400 pF	t_{I2KLKV}	$20 + 0.1 \times C_B$	250	ns	2
Pulse width of spikes which must be suppressed by the input filter	t_{I2KHKL}	0	50	ns	3
Input current each I/O pin (input voltage is between $0.1 \times OV_{DD}$ and $0.9 \times OV_{DD}$(max)	I_I	–10	10	μA	4
Capacitance for each I/O pin	C_I	—	10	pF	—

Notes:
1. Output voltage (open drain or open collector) condition = 3 mA sink current.
2. C_B = capacitance of one bus line in pF.
3. Refer to the *MPC8349EA Integrated Host Processor Family Reference Manual,* for information on the digital filter used.
4. I/O pins obstruct the SDA and SCL lines if OV_{DD} is switched off.

12.2 I²C AC Electrical Specifications

Table 39 provides the AC timing parameters for the I²C interface of the MPC8343EA. Note that all values refer to V_{IH}(min) and V_{IL}(max) levels (see Table 38).

Table 39. I²C AC Electrical Specifications

Parameter	Symbol[1]	Min	Max	Unit
SCL clock frequency	f_{I2C}	0	400	kHz
Low period of the SCL clock	t_{I2CL}	1.3	—	μs
High period of the SCL clock	t_{I2CH}	0.6	—	μs
Setup time for a repeated START condition	t_{I2SVKH}	0.6	—	μs
Hold time (repeated) START condition (after this period, the first clock pulse is generated)	t_{I2SXKL}	0.6	—	μs
Data setup time	t_{I2DVKH}	100	—	ns
Data hold time:CBUS compatible masters I²C bus devices	t_{I2DXKL}	— 0[2]	— 0.9[3]	μs

Figure 31 shows the PCI input AC timing diagram.

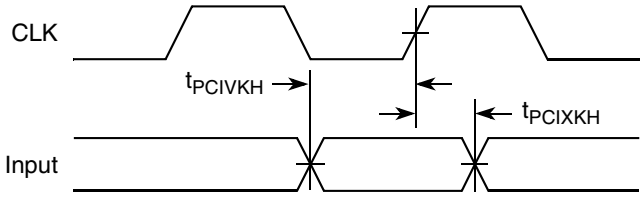


Figure 31. PCI Input AC Timing Diagram

Figure 32 shows the PCI output AC timing diagram.

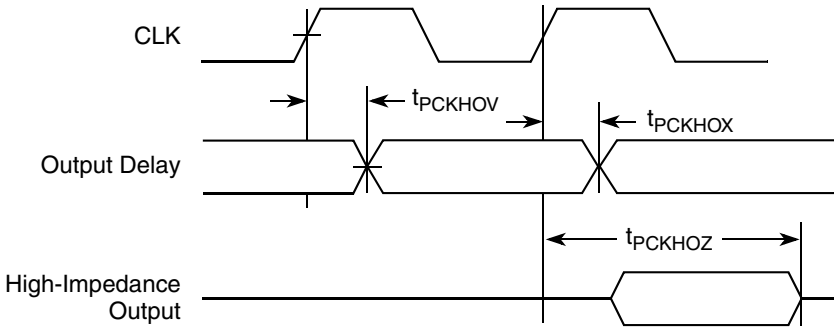


Figure 32. PCI Output AC Timing Diagram

14 Timers

This section describes the DC and AC electrical specifications for the timers.

14.1 Timer DC Electrical Characteristics

Table 43 provides the DC electrical characteristics for the MPC8343EA timer pins, including TIN, $\overline{\text{TOUT}}$, $\overline{\text{TGATE}}$, and RTC_CLK.

Table 43. Timer DC Electrical Characteristics

Parameter	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	—	—	±5	μA
Output high voltage	V_{OH}	I_{OH} = –8.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 8.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V

16 IPIC

This section describes the DC and AC electrical specifications for the external interrupt pins.

16.1 IPIC DC Electrical Characteristics

Table 47 provides the DC electrical characteristics for the external interrupt pins.

Table 47. IPIC DC Electrical Characteristics[1]

Parameter	Symbol	Condition	Min	Max	Unit	Notes
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	—	–0.3	0.8	V	—
Input current	I_{IN}	—	—	±5	μA	—
Output low voltage	V_{OL}	I_{OL} = 8.0 mA	—	0.5	V	2
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V	2

Notes:
1. This table applies for pins $\overline{\text{IRQ}}$[0:7], $\overline{\text{IRQ\_OUT}}$, and $\overline{\text{MCP\_OUT}}$.
2. $\overline{\text{IRQ\_OUT}}$ and $\overline{\text{MCP\_OUT}}$ are open-drain pins; thus V_{OH} is not relevant for those pins.

16.2 IPIC AC Timing Specifications

Table 48 provides the IPIC input and output AC timing specifications.

Table 48. IPIC Input AC Timing Specifications[1]

Parameter	Symbol[2]	Min	Unit
IPIC inputs—minimum pulse width	t_{PICWID}	20	ns

Notes:
1. Input specifications are measured at the 50 percent level of the IPIC input signals. Timings are measured at the pin.
2. IPIC inputs and outputs are asynchronous to any visible clock. IPIC outputs should be synchronized before use by external synchronous logic. IPIC inputs must be valid for at least t_{PICWID} ns to ensure proper operation in edge triggered mode.

17 SPI

This section describes the SPI DC and AC electrical specifications.

17.1 SPI DC Electrical Characteristics

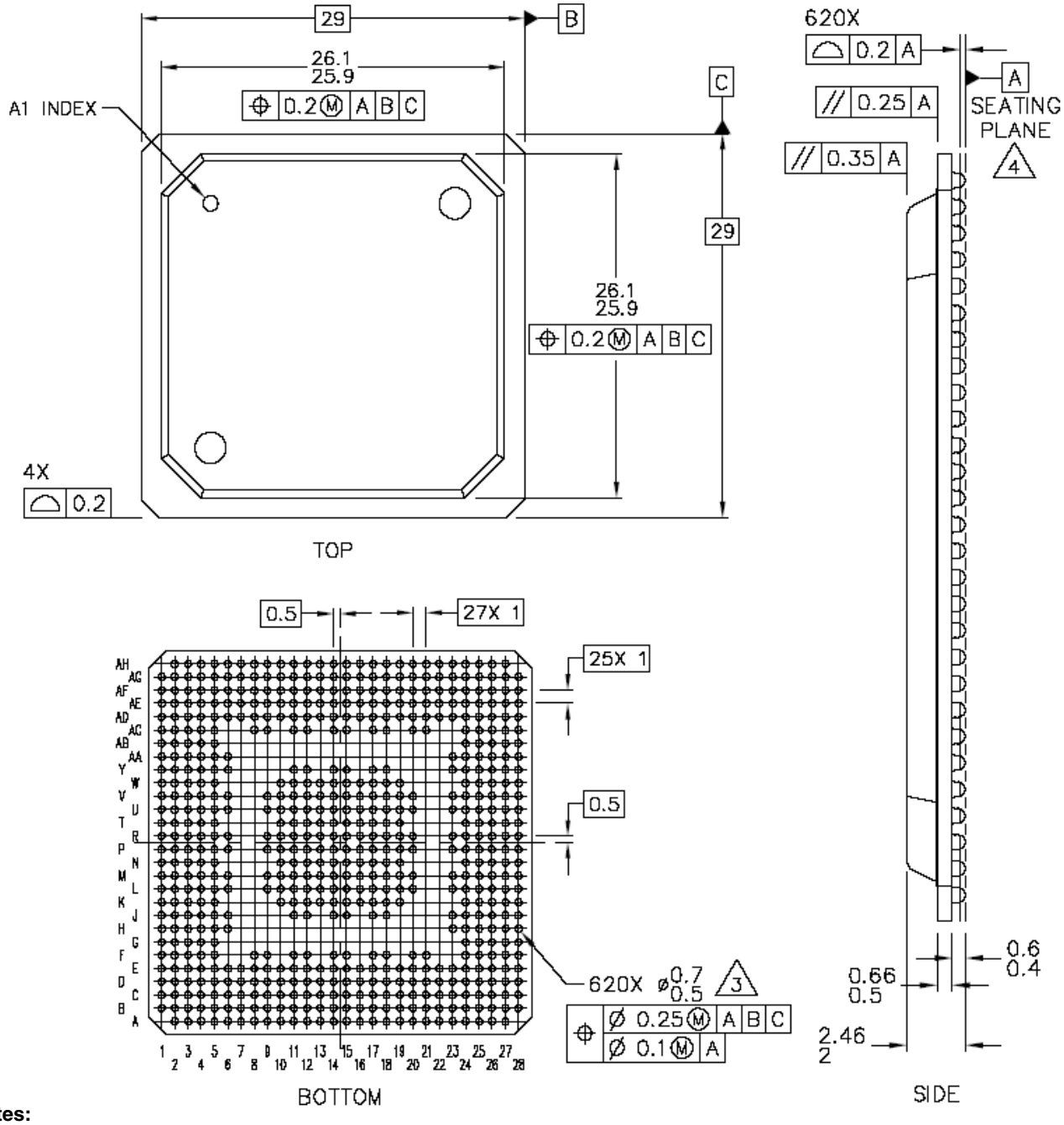
Table 49 provides the SPI DC electrical characteristics.

Table 49. SPI DC Electrical Characteristics

Parameter	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V

18.2 Mechanical Dimensions for the MPC8343EA PBGA

Figure 36 shows the mechanical dimensions and bottom surface nomenclature for the MPC8343EA, 620-PBGA package.



Notes:

1. All dimensions are in millimeters.
2. Dimensioning and tolerancing per ASME Y14. 5M-1994.
3. Maximum solder ball diameter measured parallel to datum A.
4. Datum A, the seating plane, is determined by the spherical crowns of the solder balls.

Figure 36. Mechanical Dimensions and Bottom Surface Nomenclature for the MPC8343EA PBGA

Table 51. MPC8343EA (PBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
Power and Ground Signals				
$AV_{DD}1$	C15	Power for e300 PLL (1.2 V)	$AV_{DD}1$	—
$AV_{DD}2$	U1	Power for system PLL (1.2 V)	$AV_{DD}2$	—
$AV_{DD}3$	AF9	Power for DDR DLL (1.2 V)	—	—
$AV_{DD}4$	U2	Power for LBIU DLL (1.2 V)	$AV_{DD}4$	—
GND	A2, B1, B2, D10, D18, E6, E14, E22, F9, F12, F15, F18, F21, F24, G5, H6, J23, L4, L6, L12, L13, L14, L15, L16, L17, M11, M12, M13, M14, M15, M16, M17, M18, M23, N11, N12, N13, N14, N15, N16, N17, N18, P6, P11, P12, P13, P14, P15, P16, P17, P18, P24, R5, R23, R11, R12, R13, R14, R15, R16, R17, R18, T11, T12, T13, T14, T15, T16, T17, T18, U6, U11, U12, U13, U14, U15, U16, U17, U18, V12, V13, V14, V15, V16, V17, V23, V25, W4, Y6, AA23, AB24, AC5, AC8, AC11, AC14, AC17, AC20, AD9, AD15, AD21, AE12, AE18, AF3, AF26	—	—	—
GV_{DD}	U9, V9, W10, W19, Y11, Y12, Y14, Y15, Y17, Y18, AA6, AB5, AC9, AC12, AC15, AC18, AC21, AC24, AD6, AD8, AD14, AD20, AE5, AE11, AE17, AG2, AG27	Power for DDR DRAM I/O voltage (2.5 V)	GV_{DD}	—
LV_{DD1}	U20, W25	Power for three speed Ethernet #1 and for Ethernet management interface I/O (2.5V, 3.3V)	LV_{DD1}	—
LV_{DD2}	V20, Y23	Power for three speed Ethernet #2 I/O (2.5 V, 3.3 V)	LV_{DD2}	—
V_{DD}	J11, J12, J15, K10, K11, K12, K13, K14, K15, K16, K17, K18, K19, L10, L11, L18, L19, M10, M19, N10, N19, P9, P10, P19, R10, R19, R20, T10, T19, U10, U19, V10, V11, V18, V19, W11, W12, W13, W14, W15, W16, W17, W18	Power for core (1.2 V)	V_{DD}	—

19 Clocking

Figure 37 shows the internal distribution of the clocks.

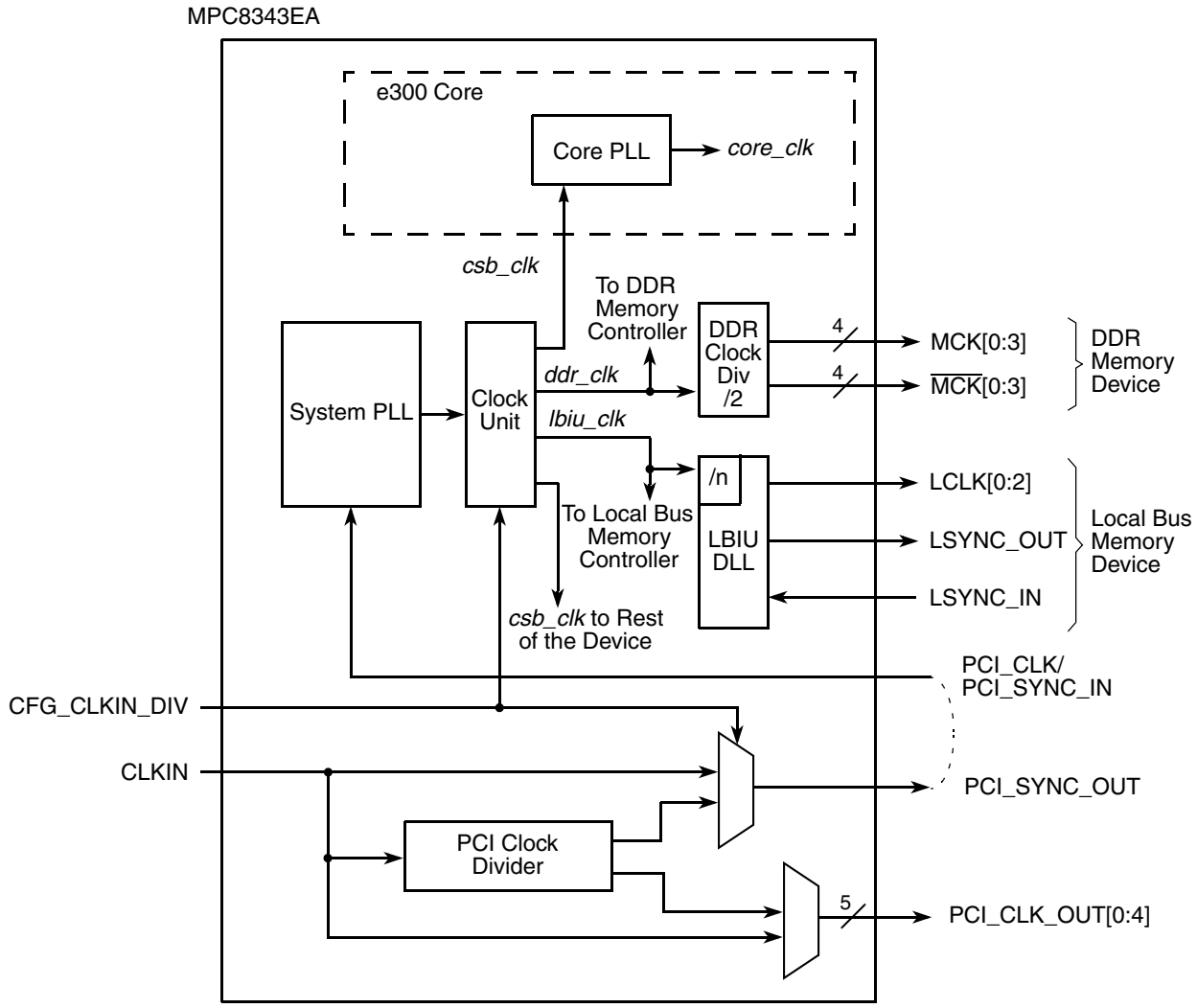


Figure 37. MPC8343EA Clock Subsystem

The primary clock source can be one of two inputs, CLKIN or PCI_CLK, depending on whether the device is configured in PCI host or PCI agent mode. When the MPC8343EA is configured as a PCI host device, CLKIN is its primary input clock. CLKIN feeds the PCI clock divider (÷2) and the multiplexors for PCI_SYNC_OUT and PCI_CLK_OUT. The CFG_CLKIN_DIV configuration input selects whether CLKIN or CLKIN/2 is driven out on the PCI_SYNC_OUT signal. The OCCR[PCICD*n*] parameters select whether CLKIN or CLKIN/2 is driven out on the PCI_CLK_OUT*n* signals.

PCI_SYNC_OUT is connected externally to PCI_SYNC_IN to allow the internal clock subsystem to synchronize to the system PCI clocks. PCI_SYNC_OUT must be connected properly to PCI_SYNC_IN, with equal delay to all PCI agent devices in the system, to allow the MPC8343EA to function. When the device is configured as a PCI agent device, PCI_CLK is the primary input clock and the CLKIN signal should be tied to GND.

Table 58. Suggested PLL Configurations (continued)

Ref No.[1]	RCWL		266 MHz Device			333 MHz Device			400 MHz Device		
	SPMF	CORE PLL	Input Clock Freq (MHz)[2]	CSB Freq (MHz)	Core Freq (MHz)	Input Clock Freq (MHz)[2]	CSB Freq (MHz)	Core Freq (MHz)	Input Clock Freq (MHz)[2]	CSB Freq (MHz)	Core Freq (MHz)
326	**0011**	**0100110**	—			33	100	300	33	100	300
623	**0110**	**0100011**	—			33	200	300	33	200	300
922	**1001**	**0100010**	—			33	300	300	33	300	300
425	**0100**	**0100101**	—			33	133	333	33	133	333
524	**0101**	**0100100**	—			33	166	333	33	166	333
A22	**1010**	**0100010**	—			33	333	333	33	333	333
723	**0111**	**0100011**	—			—			33	233	350
604	**0110**	**0000100**	—			—			33	200	400
624	**0110**	**0100100**	—			—			33	200	400
823	1000	0100011	—			—			33	266	400
66 MHz CLKIN/PCI_CLK Options											
242	**0010**	**1000010**	66	133	133	66	133	133	66	133	133
322	**0011**	**0100010**	66	200	200	66	200	200	66	200	200
224	**0010**	**0100100**	66	133	266	66	133	266	66	133	266
422	**0100**	**0100010**	66	266	266	66	266	266	66	266	266
323	**0011**	**0100011**	—			66	200	300	66	200	300
223	**0010**	**0100101**	—			66	133	333	66	133	333
522	**0101**	**0100010**	—			66	333	333	66	333	333
304	**0011**	**0000100**	—			—			66	200	400
324	**0011**	**0100100**	—			—			66	200	400
403	**0100**	**0000011**	—			—			66	266	400
423	**0100**	**0100011**	—			—			66	266	400

1 The PLL configuration reference number is the hexadecimal representation of RCWL, bits 4–15 associated with the SPMF and COREPLL settings given in the table.

2 The input clock is CLKIN for PCI host mode or PCI_CLK for PCI agent mode.

that the thermocouple junction rests on the package. A small amount of epoxy is placed over the thermocouple junction and over about 1 mm of wire extending from the junction. The thermocouple wire is placed flat against the package case to avoid measurement errors caused by cooling effects of the thermocouple wire.

20.2.4 Heat Sinks and Junction-to-Case Thermal Resistance

Some application environments require a heat sink to provide the necessary thermal management of the device. When a heat sink is used, the thermal resistance is expressed as the sum of a junction-to-case thermal resistance and a case-to-ambient thermal resistance:

$$R_{\theta JA} = R_{\theta JC} + R_{\theta CA}$$

where:

$R_{\theta JA}$ = junction-to-ambient thermal resistance (°C/W)
$R_{\theta JC}$ = junction-to-case thermal resistance (°C/W)
$R_{\theta CA}$ = case-to-ambient thermal resistance (°C/W)

$R_{\theta JC}$ is device-related and cannot be influenced by the user. The user controls the thermal environment to change the case-to-ambient thermal resistance, $R_{\theta CA}$. For instance, the user can change the size of the heat sink, the air flow around the device, the interface material, the mounting arrangement on printed-circuit board, or change the thermal dissipation on the printed-circuit board surrounding the device.

The thermal performance of devices with heat sinks has been simulated with a few commercially available heat sinks. The heat sink choice is determined by the application environment (temperature, air flow, adjacent component power dissipation) and the physical space available. Because there is not a standard application environment, a standard heat sink is not required.

Table 60 shows heat sink thermal resistance for PBGA of the MPC8343EA.

Table 60. Heat Sink and Thermal Resistance of MPC8343EA (PBGA)

Heat Sink Assuming Thermal Grease	Air Flow	29 × 29 mm PBGA
		Thermal Resistance
AAVID 30 × 30 × 9.4 mm pin fin	Natural convection	13.5
AAVID 30 × 30 × 9.4 mm pin fin	1 m/s	9.6
AAVID 30 × 30 × 9.4 mm pin fin	2 m/s	8.8
AAVID 31 × 35 × 23 mm pin fin	Natural convection	11.3
AAVID 31 × 35 × 23 mm pin fin	1 m/s	8.1
AAVID 31 × 35 × 23 mm pin fin	2 m/s	7.5
Wakefield, 53 × 53 × 25 mm pin fin	Natural convection	9.1
Wakefield, 53 × 53 × 25 mm pin fin	1 m/s	7.1
Wakefield, 53 × 53 × 25 mm pin fin	2 m/s	6.5
MEI, 75 × 85 × 12 no adjacent board, extrusion	Natural convection	10.1

23 Document Revision History

This table provides a revision history of this document.

Table 64. Document Revision History

Rev. Number	Date	Substantive Change(s)
11	09/2011	• In Section 2.2, "Power Sequencing," added Section 2.2.1, "Power-Up Sequencing" and Figure 4. • In Table 25, Table 29, and Table 27, removed the GTX_CLK125. • In Table 30, updated t_{MDKHDX} Max value from 170ns to 70ns.
10	11/2010	• In Table 51, added overbar to $\overline{LCS}$[4] and $\overline{LCS}$[5] signals. In Table 51 added note for pin LGPL4. • In Section 21.7, "Pull-Up Resistor Requirements, updated the list of open drain type pins.
9	05/2010	• In Table 25 through Table 26, changed V_{IL}(min) to V_{IH}(max) to (20%–80%). • Added Table 8, "EC_GTX_CLK125 AC Timing Specifications."
8	5/2009	• In Section 18.1, "Package Parameters for the MPC8343EA PBGA, changed solder ball for TBGA and PBGA from 95.5 Sn/0.5 Cu/4 Ag to 96.5 Sn/3.5 Ag. • In Table 53, added two columns for the DDR1 and DDR2 memory bus frequency. • In Table 62, footnote 1, changed 667(TBGA) to 533(TBGA). footnote 4, added data rate for DDR1 and DDR2.
7	2/2009	• Added footnote 6 to Table 7. • In Section 9.2, "USB AC Electrical Specifications," clarified that AC table is for ULPI only. • In Table 35, corrected t_{LBKHOV} parameter to t_{LBKLOV} (output data is driven on falling edge of clock in DLL bypass mode). Similarly, made the same correction to Figure 18, Figure 20, and Figure 21 for output signals. • Added footnote 10 to Table 51. • In Table 51, updated note 11 to say the following: "SEC1_TXD[3] is required an external pull-up resistor. For proper functionality of the device, this pin must be pulled up or actively driven high during a hard reset. No external pull-down resistors are allowed to be attached to this net." • In Section 21.1, "System Clocking," removed "(AVDD1)" and "(AVDD2") from bulleted list. • In Section 21.2, "PLL Power Supply Filtering," in the second paragraph, changed "provide five independent filter circuits," and "the five AVDD pins" to provide four independent filter circuits," and "the four AVDD pins." • In Table 62, updated note 1 to say the following: "For temperature range = C, processor frequency is limited to 400 with a platform frequency of 266."
6	4/2007	• In Table 3, "Output Drive Capability," changed the values in the Output Impedance column and added USB to the seventh row. • In Section 21.7, "Pull-Up Resistor Requirements,"deleted last two paragraphs and after first paragraph, added a new paragraph. • Deleted Section 21.8, "JTAG Configuration Signals," and Figure 43, "JTAG Interface Connection."
5	3/2007	• Page 1, updated first paragraph to reflect PowerQUICC II Pro information. • In Table 18, "DDR and DDR2 SDRAM Input AC Timing Specifications," added note 2 to t_{CISKEW} and deleted original note 3; renumbered the remaining notes. • In Figure 38, "JTAG Interface Connection," updated with new figure. • In Figure 38, "JTAG Interface Connection," updated with new figure. • In Section 23, "Ordering Information," replaced first paragraph and added a note. • In Section 23.1, "Part Numbers Fully Addressed by this Document," replaced first paragraph.
4	12/2006	Table 19, "DDR and DDR2 SDRAM Output AC Timing Specifications," modified T_{ddkhds} for 333 MHz from 900 ps to 775 ps.

Table 64. Document Revision History (continued)

Rev. Number	Date	Substantive Change(s)
3	11/2006	• Updated note in introduction. • In the features list in Section 1, “Overview,” updated DDR data rate to show 266 MHz for PBGA parts for all silicon revisions. • In Table 57, “Suggested PLL Configurations,” added the following row: • Ref No: 823, SPMF: 1000, Core PLL: 0100011, 400-MHz Device Input Clock Freq: 33, CSB Freq: 266, and Core Freq: 400. • In Section 23, “Ordering Information,” replicated note from document introduction.
2	8/2006	• Changed all references to revision 2.0 silicon to revision 3.0 silicon. • Changed number of general purpose parallel I/O pins to 39 in Section 1, “Overview.” • Changed VIH minimum value in Table 35, “JTAG Interface DC Electrical Characteristics,” to OV_{DD} – 0.3. • In Table 40, “PCI DC Electrical Characteristics,” changed high-level input voltage values to min = 2 and max = OV_{DD} + 0.3; changed low-level input voltage values to min = (–0.3) and max = 0.8. • In Table 44, “PCI DC Electrical Characteristics,” changed high-level input voltage values to min = 2 and max = OV_{DD} + 0.3; changed low-level input voltage values to min = (–0.3) and max = 0.8. • In Table 44, “PCI DC Electrical Characteristics,” changed high-level input voltage values to min = 2 and max = OV_{DD} + 0.3; changed low-level input voltage values to min = (–0.3) and max = 0.8. • Updated DDR2 I/O power values in Table 5, “MPC8347EA Typical I/O Power Dissipation.” •
1	4/2006	• Removed Table 20, “Timing Parameters for DDR2-400.” • Changed ADDR/CMD to ADDR/CMD/MODT in Table 9, “DDR and DDR2 SDRAM Output AC Timing Specifications,” rows 2 and 3, and in Figure 2, “DDR SDRAM Output Timing Diagram. • Changed Min and Max values for V_{IH} and VIL in Table 40Table 44,“PCI DC Electrical Characteristics.” • In Table 58, “MPC8343EA (PBGA) Pinout Listing,” and Table 52, “MPC8347EA (PBGA) Pinout Listing,” modified rows for MDICO and MDIC1 signals and added note ‘It is recommended that MDICO be tied to GRD using an 18 Ω resistor and MCIC1 be tied to DDR power using an 18 Ω resistor.’ • Table 58, “MPC8343EA (PBGA) Pinout Listing,” in row AVDD3 changed power supply from “AVDD3” to ‘—.’
0	3/2006	Initial public release